#### 20 m $\Omega$ , Fast Turn On, 2.5 A Load Switch with Discharge



#### **General Description**

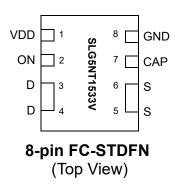
The SLG5NT1533V is a 20 mQ 2.5 A single-channel load switch with configurable slew rate control. The device can enable fast power rail turn on with big cap loading. Internal circuit limits max inrush current to prevent device damage. The product is packaged in an ultra-small 1.0 x 1.6 mm package.

#### **Features**

- 1.0 x 1.6 x 0.55 mm FC-STDFN package (2 fused pins for drain and 2 fused pins for source)
- Logic level ON pin capable of supporting 0.85 V CMOS Logic
- · Discharged Load when off
- · Fast Turn On time
  - 32  $\mu$ s, C<sub>SLEW</sub> = 0.1 nF, C<sub>LOAD</sub> = 1  $\mu$ F, I<sub>DS</sub> = 100 mA + 102  $\mu$ s, C<sub>SLEW</sub> = 0.5 nF, C<sub>LOAD</sub> = 10  $\mu$ F, I<sub>DS</sub> = 2.5 A
- Low RDS<sub>ON</sub> while supporting 2.5 A

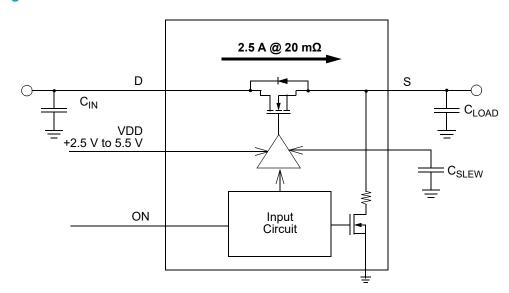
  - 20 m $\Omega$ , V<sub>DD</sub> = 5 V, V<sub>D</sub> = 1 V 27.5 mΩ, V<sub>DD</sub> = 3.3 V, V<sub>D</sub> = 1 V
- · Pb-Free / Halogen-Free / RoHS compliant
- Operating Temperature: -40 °C to 85°C
- Operating Voltage: 2.5 V to 5.5 V
- Power Rail Switching  $V_D = 0.85$  V to  $V_D = V_{DD} 1.5$  V

#### **Pin Configuration**



#### **Applications**

- Fast Turn On/Off power rail switching with big load capacitance
- Frequent wake & sleep power cycle
- Mobile devices and portable devices



Datasheet Revision 1.07			
	Datasheet	Revision 1.07	

### **Block Diagram**

3-Feb-2022

### 20 mΩ, Fast Turn On, 2.5 A Load Switch with Discharge



### **Pin Description**

Pin #	Pin Name	Туре	Pin Description
1	VDD	PWR	VDD supplies the power for the operation of the load switch and internal control circuitry. Bypass the VDD pin to GND with a 0.1 $\mu F$ (or larger) capacitor.
2	ON	Input	A low-to-high transition on this pin initiates the operation of the SLG5NT1533V's state machine. ON is a CMOS input with ON_V <sub>IL</sub> < 0.3 V and ON_V <sub>IH</sub> > 0.85 V thresholds. While there is an internal pull-down circuit to GND (~4 M $\Omega$ ), connect this pin directly to a general-purpose output (GPO) of a microcontroller, an application processor, or a system controller.
3, 4	D	MOSFET	Drain terminal connection of the n-channel MOSFET (2 pins fused for V <sub>D</sub> ). Connect at least a low-ESR 0.1 $\mu$ F capacitor from this pin to ground. Capacitors used at V <sub>D</sub> should be rated at 10 V or higher.
5, 6	S	MOSFET	Source terminal connection of the n-channel MOSFET (2 pins fused for $V_S$ ). Connect a low-ESR capacitor from this pin to ground and consult the Electrical Characteristics table for recommended C <sub>LOAD</sub> range. Capacitors used at V <sub>S</sub> should be rated at 10 V or higher.
7	CAP	Input	A low-ESR, stable dielectric, ceramic surface-mount capacitor connected from CAP pin to GND sets the $V_S$ slew rate and overall turn-on time of the SLG5NT1533V. Capacitors at CAP pin should be rated at 10 V or higher.
8	GND	GND	Ground connection. Connect this pin to system analog or power ground plane.

### **Ordering Information**

Part Number	Туре	Production Flow
SLG5NT1533V	FC-STDFN 8L	Industrial, -40 °C to 85 °C
SLG5NT1533VTR	FC-STDFN 8L (Tape and Reel)	Industrial, -40 °C to 85 °C



### 20 mΩ, Fast Turn On, 2.5 A Load Switch with Discharge

### **Absolute Maximum Ratings**

Parameter	Description	Conditions	Min.	Тур.	Max.	Unit
V <sub>DD</sub>	Power Supply				7	V
V <sub>D</sub> to GND	Load Switch Input Voltage to GND		-0.3		$V_{DD}$	V
V <sub>S</sub> to GND	Load Switch Output Voltage to GND		-0.3		V <sub>D</sub>	V
ON and CAP to GND	ON and CAP Pin Voltages to GND		-0.3		$V_{DD}$	V
Τ <sub>S</sub>	Storage Temperature		-65		150	°C
TJ	Junction Temperature				150	°C
ESD <sub>HBM</sub>	ESD Protection	Human Body Model	2000			V
MSL	Moisture Sensitivity Level			1	L	
θ <sub>JA</sub>	Thermal Resistance	1.6 x 1 mm, 8L STDFN; Determined using 1 in <sup>2</sup> , 1 oz. copper pads under each VD and VS terminals and FR4 pcb material		75		°C/W
W <sub>DIS</sub>	Package Power Dissipation				0.4	W
		For no more than 20 $\mu s$ with 1% duty cycle			25.0	А
MOSFET IDS <sub>PK</sub>	Peak Current from Drain to Source	For no more than 50 µs with 1% duty cycle			12.5	А
		For no more than 1 ms with 1% duty cycle			3.5	А
only and fur	nctional operation of the device at thes	Maximum Ratings" may cause permanent damagese or any other conditions above those indicate aximum rating conditions for extended periods r	ed in the	operation	al sectior	

### **Electrical Characteristics**

 $T_A$  = -40 °C to 85 °C. Typical values are at  $T_A$  = 25 °C unless otherwise noted.

Parameter	Description	Conditions	Min.	Тур.	Max.	Unit
V <sub>DD</sub>	Power Supply Voltage	-40 °C to 85 °C	2.5		5.5	V
1	Power Supply Current (PIN 1)	when OFF			1	μA
I <sub>DD</sub>		when ON, No load			10	μA
		$V_{DD}$ = 5 V, $V_D$ = 1.0 V, $V_{DD}$ - $V_D$ = 4.0 V, $R_{LOAD}$ = 0.5 Ω		20	24	mΩ
		$V_{DD}$ = 3.3 V, $V_D$ = 1.0 V, $V_{DD}$ - $V_D$ = 2.3 V, $R_{LOAD}$ = 0.5 Ω		27.5	31	mΩ
RDS <sub>ON</sub>	ON Resistance, T <sub>A</sub> = 70°C	$V_{DD}$ = 5 V, $V_D$ = 1.0 V, $V_{DD}$ - $V_D$ = 4.0 V, $R_{LOAD}$ = 0.5 Ω		23.5	27	mΩ
ND3 <sub>ON</sub>	on resistance, T <sub>A</sub> = 70 C	$V_{DD}$ = 3.3 V, $V_D$ = 1.0 V, $V_{DD}$ - $V_D$ = 2.3 V, $R_{LOAD}$ = 0.5 Ω		31	35	mΩ
	ON Resistance, $T_A = 85^{\circ}C$	$V_{DD}$ = 5 V, $V_D$ = 1.0 V, $V_{DD}$ - $V_D$ = 4.0 V, $R_{LOAD}$ = 0.5 Ω		24.5	28	mΩ
	$CN$ Resistance, $T_A = 00^{\circ}$ C	$V_{DD}$ = 3.3 V, $V_D$ = 1.0 V, $V_{DD}$ - $V_D$ = 2.3 V, $R_{LOAD}$ = 0.5 Ω		33	37	mΩ
MOSFET IDS	Current from D to S	Continuous, $V_D$ = 0.85 V to 3.3 V			2.5	А
V <sub>D</sub>	Drain Voltage		0.85		V <sub>DD</sub> - 1.5	V

Da	tas	he	et	



### 20 mΩ, Fast Turn On, 2.5 A Load Switch with Discharge

#### **Electrical Characteristics (continued)**

 $T_A$  = -40 °C to 85 °C. Typical values are at  $T_A$  = 25 °C unless otherwise noted.

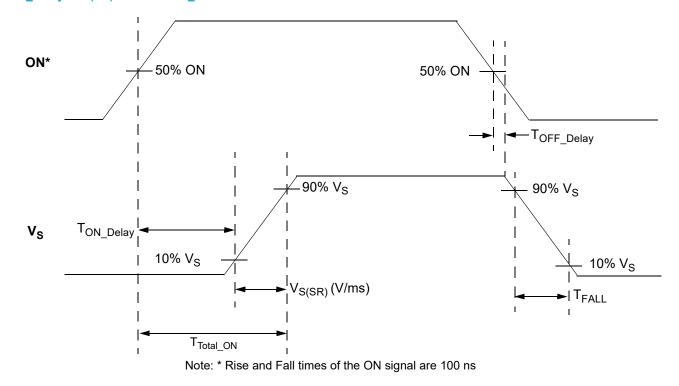
Parameter	Description	Conditions	Min.	Тур.	Max.	Unit
	ON Delay Time	50% ON to 10% V <sub>S</sub> , V <sub>DD</sub> = 5 V, V <sub>D</sub> = 1.0 V, C <sub>SLEW</sub> = 0.1 nF		12	15	μs
T <sub>ON_Delay</sub>	On Delay Time	50% ON to 10% V <sub>S</sub> , V <sub>DD</sub> = 5 V, V <sub>D</sub> = 1.0 V, C <sub>SLEW</sub> = 0.5 nF		32	35	μs
		50% ON to 90% V <sub>S</sub>	Set by	External	C <sub>SLEW</sub> <sup>1</sup>	μs
		50% ON to 90% $V_{S}$ , $V_{DD}$ = 5 V, $V_{D}$ = 1.0 V, $C_{LOAD}$ = 1 µF, $I_{DS}$ = 50 mA, $C_{SLEW}$ = 0.1 nF		32	39	μs
T <sub>Total_ON</sub>	Total Turn On Time	50% ON to 90% $V_{S}$ , $V_{DD}$ = 5 V, $V_{D}$ = 1.0 V, $C_{LOAD}$ = 1 µF, $I_{DS}$ = 100 mA, $C_{SLEW}$ = 0.1 nF		32	39	μs
		50% ON to 90% $V_{S,} V_{DD}$ = 5 V, $V_{D}$ = 1.0 V, $C_{LOAD}$ = 4.7 µF, $I_{DS}$ = 2.5 A, $C_{SLEW}$ = 0.5 nF		102	123	μs
	50% ON to 90% $V_{S,} V_{DD} = 5 V$ , $V_{D} = 1.0 V$ , $C_{LOAD} = 10 \mu$ F, $I_{DS} = 2.5 A$ , $C_{SLEW} = 0.5 n$ F		102	123	μs	
		10% V_S to 90% V_S	Set by	External	C <sub>SLEW</sub> <sup>1</sup>	V/m
	Slew Rate	$\begin{array}{l} 10\% \ V_S \ to \ 90\% \ V_S, \ V_{DD} = 5 \ V, \\ V_D = 1.0 \ V, \ C_{LOAD} = 1 \ \mu F, \\ I_{DS} = 50 \ m A, \ C_{SLEW} = 0.1 \ n F \end{array}$		65	78	V/m:
V <sub>S(SR)</sub> Slew Rate				65	78	V/m
	10% V <sub>S</sub> to 90% V <sub>S</sub> , V <sub>DD</sub> = 5 V, V <sub>D</sub> = 1.0 V, C <sub>LOAD</sub> = 4.7 $\mu$ F, I <sub>DS</sub> = 2.5 A, C <sub>SLEW</sub> = 0.5 nF		13	16	V/m	
		$\begin{array}{l} 10\% \ V_S \ to \ 90\% \ V_S, \ V_{DD} = 5 \ V, \\ V_D = 1.0 \ V, \ C_{LOAD} = 10 \ \mu\text{F}, \\ I_{DS} = 2.5 \ \text{A}, \ C_{SLEW} = 0.5 \ \text{nF} \end{array}$		13.5	16.5	V/m
C <sub>LOAD</sub>	Output Load Capacitance	C <sub>LOAD</sub> connected from S to GND			10	μF
R <sub>DISCHRGE</sub>	Discharge Resistance		100	150	300	Ω
$ON_V_{IH}$	High Input Voltage on ON pin		0.85		V <sub>DD</sub>	V
ON_V <sub>IL</sub>	Low Input Voltage on ON pin		-0.3	0	0.3	V
T <sub>OFF_Delay</sub>	OFF Delay Time	50% ON to V <sub>S</sub> Fall Start, no C <sub>LOAD</sub> , R <sub>LOAD</sub> = 20 $\Omega$ , V <sub>DD</sub> = 5 V, V <sub>D</sub> = 1.0 V, No C <sub>SLEW</sub>		120	150	μs
THERM <sub>OFF</sub>	Thermal shutoff turn-off temperature	Programmable, automatic shutoff temperature		125		°C
HERMOFFACC	Thermal Sensor Accuracy				±20	%
THERM <sub>DT</sub>	Thermal Disable Time	Thermal sensor disable for the ON rising edge to 100 µs. Prevent thermal shutdown from inrush current			100	μs

**Datasheet** 



20 mΩ, Fast Turn On, 2.5 A Load Switch with Discharge

# $T_{ON\_Delay},\,V_{S(SR)}\!,$ and $T_{Total\_ON}$ Timing Details

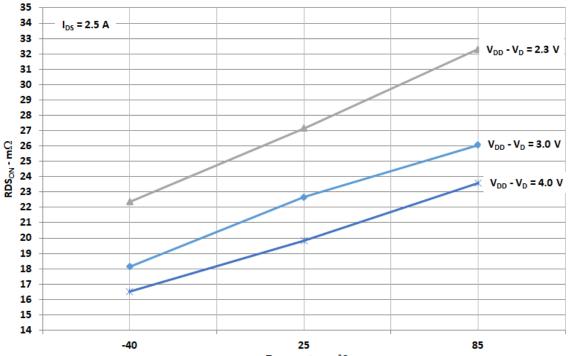




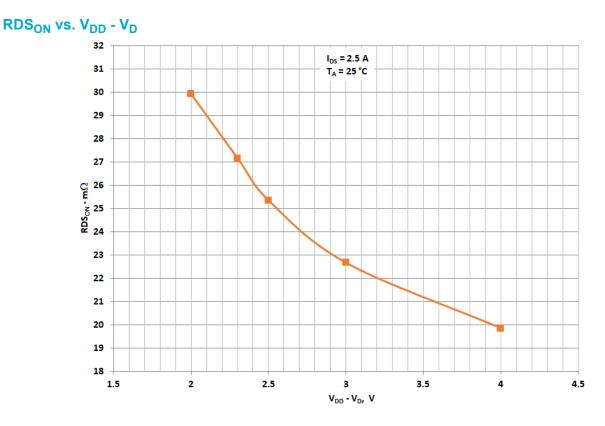
20 m $\Omega$ , Fast Turn On, 2.5 A Load Switch with Discharge

#### **Typical Performance Characteristics**

### RDS<sub>ON</sub> vs. Temperature and V<sub>DD</sub> - V<sub>D</sub>





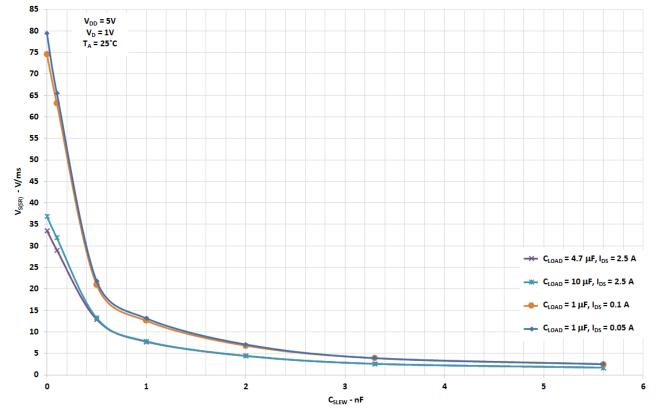


#### Datasheet

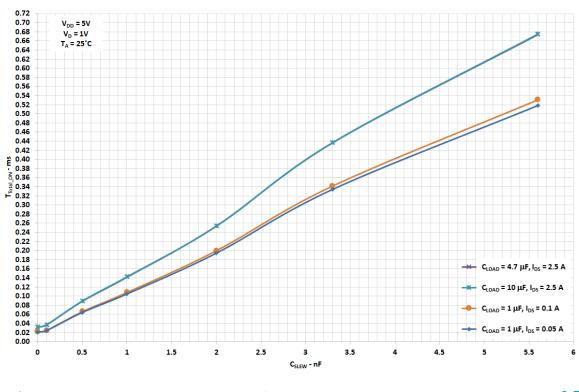


# 20 m $\Omega$ , Fast Turn On, 2.5 A Load Switch with Discharge

### V<sub>S</sub> Slew Rate vs. C<sub>SLEW</sub>



### T<sub>Total\_ON</sub> vs. C<sub>SLEW</sub>





# 20 m $\Omega$ , Fast Turn On, 2.5 A Load Switch with Discharge

#### SLG5NT1533V Power-Up/Power-Down Sequence Considerations

A nominal power-up sequence is to apply  $V_{DD}$  first, followed by  $V_D$  only after  $V_{DD}$  is > 90 % of final  $V_{DD}$ , and finally toggling the ON pin LOW-to-HIGH after  $V_D$  is at least 90% of its final value.

A nominal power-down sequence is the power-up sequence in reverse order.

If  $V_{DD}$  and  $V_D$  are applied at the same time, a voltage glitch may appear on the output pin at  $V_S$ . To prevent glitches at the output, it is recommended to connect at least a 1  $\mu$ F capacitor from the S pin to GND and to keep the  $V_{DD}$  and  $V_D$  ramp times higher than 2 ms.

If the ON pin is toggled HIGH before V<sub>DD</sub> and V<sub>D</sub> have reached their steady-state values the load switch timing parameters may differ from datasheet specifications.

#### **Power Dissipation**

The junction temperature of the SLG5NT1533V depends on different factors such as board layout, ambient temperature, and other environmental factors. The primary contributor to the increase in the junction temperature of the SLG5NT1533V is the power dissipation of its power MOSFET. Its power dissipation and the junction temperature in nominal operating mode can be calculated using the following equations:

$$PD = (RDS_{ON} \times I_{DS}^{2}) + (V_{DD} \times I_{DD})$$

where:

 $\begin{array}{l} \mathsf{PD} = \mathsf{Power dissipation, in Watts (W)} \\ \mathsf{RDS}_{\mathsf{ON}} = \mathsf{Power MOSFET ON resistance, in Ohms (\Omega)} \\ \mathsf{I}_{\mathsf{DS}} = \mathsf{Output current, in Amps (A)} \\ \mathsf{V}_{\mathsf{DD}} = \mathsf{Power supply voltage applied to the SLG5NT1533V, in Volts (V)} \\ \mathsf{I}_{\mathsf{DD}} = \mathsf{Power supply current of the SLG5NT1533V at V_{\mathsf{DD}}, in Amps (A)} \end{array}$ 

and

$$T_J = PD \times \theta_{JA} + T_A$$

where:

T<sub>1</sub> = Junction temperature, in Celsius degrees (°C)

 $\theta_{JA}$  = Package thermal resistance, in Celsius degrees per Watt (°C/W) = 75 °C/W for the SLG5NT1533V's STDFN package. T<sub>A</sub> = Ambient temperature, in Celsius degrees (°C)

For more information on GreenFET load switch features, please visit our website and see App Note "AN-1068 GreenFET and High Voltage GreenFET Load Switch Basics".

atasheet		
----------	--	--

D



20 m $\Omega$ , Fast Turn On, 2.5 A Load Switch with Discharge

#### Layout Guidelines:

- 1. The VDD pin needs a 0.1µF (or larger) external capacitor to smooth pulses from the power supply. Locate this capacitor as close as possible to the SLG5NT1533V's pin 1.
- 2.Since the D and S pins dissipate most of the heat generated during high-load current operation, it is highly recommended to make power traces as short, direct, and wide as possible. A good practice is to make power traces with <u>absolute minimum</u> <u>widths</u> of 15 mils (0.381 mm) per Ampere. A representative layout, shown in Figure 1, illustrates proper techniques for heat to transfer as efficiently as possible out of the device;
- 3.To minimize the effects of parasitic trace inductance on normal operation, it is recommended to connect input  $C_{IN}$  and output  $C_{LOAD}$  low-ESR capacitors as close as possible to the SLG5NT1533V's D and S pins;
- 4. The GND pin should be connected to system analog or power ground plane.
- 5. 2 oz. copper is recommended for high current operation.

#### SLG5NT1533V Evaluation Board:

Please solder your SLG5NT1533V here

A GFET3 Evaluation Board for SLG5NT1533V is designed according to the statements above and is illustrated on Figure 1. Please note that evaluation board has D\_Sense and S\_Sense pads. They cannot carry high currents and dedicated only for RDS<sub>ON</sub> evaluation.

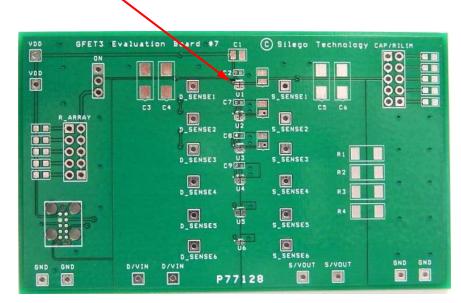


Figure 1. SLG5NT1533V Evaluation Board

Da	<b>4</b> -			
1 1 2		en	00	
20		311		



20 mΩ, Fast Turn On, 2.5 A Load Switch with Discharge

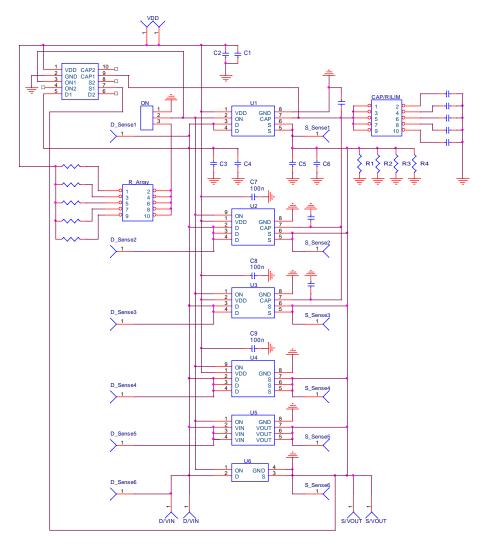


Figure 2. SLG5NT1533V Evaluation Board Connection Circuit

D.	- 4 -			4
	ata	SI	ee	Τ.
		911	<b>U</b> U	•

**Revision 1.07** 



20 m $\Omega$ , Fast Turn On, 2.5 A Load Switch with Discharge

### **Basic Test Setup and Connections**

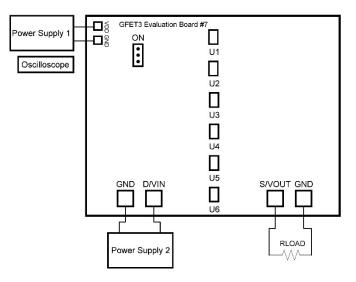


Figure 3. SLG5NT1533V Evaluation Board Connection Circuit

#### **EVB** Configuration

- 1. Connect oscilloscope probes to D/VIN, S/VOUT, ON, etc.;
- 2. Turn on Power Supply 1 and set desired  $V_{DD}$  from 2.5 V...5.5 V range;
- 3. Turn on Power Supply 2 and set desired  $V_D$  from 0.85 V…V\_{DD} 1.5 V range;
- 4 .Toggle the ON signal High or Low to observe SLG5NT1533V operation.



20 mΩ, Fast Turn On, 2.5 A Load Switch with Discharge

### Package Top Marking System Definition

	ABC	Serial Number
Pin 1 Identifier	0	

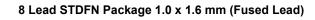
Each character in Serial Number field can be alphanumeric A-Z

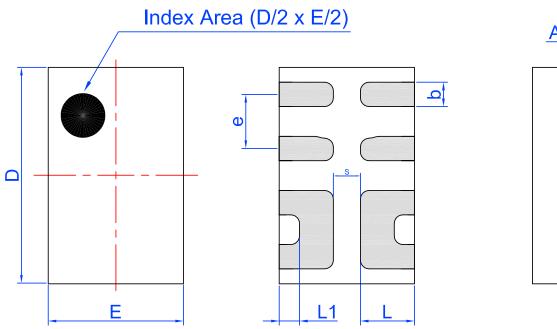
Datasheet	1

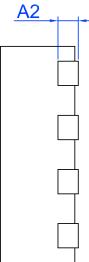


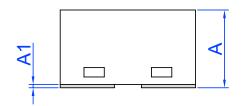
20 mΩ, Fast Turn On, 2.5 A Load Switch with Discharge

### **Package Drawing and Dimensions**









### Unit: mm

Symbol	Min	Nom.	Max	Symbol	Min	Nom.	Max	
A	0.50	0.55	0.60	D	1.55	1.60	1.65	
A1	0.005	-	0.060	E	0.95	1.00	1.05	
A2	0.10	0.15	0.20	L	0.35	0.40	0.45	
b	0.13	0.18	0.23	L1	0.10	0.15	0.20	
е	(	).40 BSC	,	S	0.2 REF			

	-	ta	-		-	-	4	
	F.	тя	9	п	ρ		т.	
-	•		-		-	<u> </u>	•	



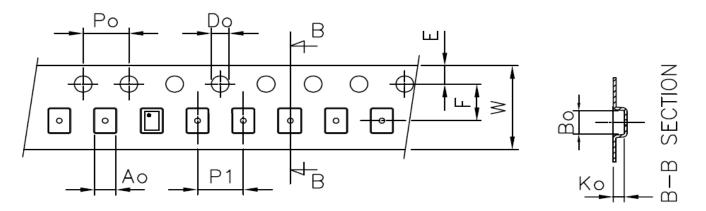
20 mΩ, Fast Turn On, 2.5 A Load Switch with Discharge

### **Tape and Reel Specifications**

Package	# of	Nominal	Max Units		Reel &	Leader (min)		Trailer (min)		Таре	Part
Туре	Pins	Package Size [mm]	per Reel	per Box	Hub Size [mm]	Pockets	Length [mm]	Pockets	Length [mm]	Width [mm]	Pitch [mm]
STDFN 8I 1x1.6mm 0.4P FC Green	8	1.0 x 1.6 x 0.55	3,000	3,000	178 / 60	100	400	100	400	8	4

### **Carrier Tape Drawing and Dimensions**

Package Type	PocketBTM Length	PocketBTM Width	Pocket Depth	Index Hole Pitch	Pocket Pitch	Index Hole Diameter	Index Hole to Tape Edge	Index Hole to Pocket Center	Tape Width
	A0	B0	К0	P0	P1	D0	E	F	W
STDFN 8L 1x1.6mm 0.4P FC Green	1.12	1.72	0.7	4	4	1.55	1.75	3.5	8



### **Recommended Reflow Soldering Profile**

Please see IPC/JEDEC J-STD-020: latest revision for reflow profile based on package volume of 0.88 mm<sup>3</sup> (nominal). More information can be found at www.jedec.org.



### 20 mΩ, Fast Turn On, 2.5 A Load Switch with Discharge

### **Revision History**

Date	Version	Change			
2/3/2022	1.07	Updated Company name and logo Fixed typos			
11/26/2018	1.06	ded Junction Temperature to Abs Max Table			
11/8/2018	1.05	Updated Style and formatting Updated Abs, Max and Electrical Characteristics tables Added Applications information Added Layout Guidelines			
8/14/2015	1.04	Add support for 0.85 VD			
4/22/2015	1.03	Removed TBD from Timing Diagram			
4/20/2015	1.02	Fixed Block Diagram (added Discharge Resistor)			
9/15/2014	1.01	Added MSL			
6/16/2014	1.0	roduction release			

#### IMPORTANT NOTICE AND DISCLAIMER

RENESAS ELECTRONICS CORPORATION AND ITS SUBSIDIARIES ("RENESAS") PROVIDES TECHNICAL SPECIFICATIONS AND RELIABILITY DATA (INCLUDING DATASHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS OR IMPLIED, INCLUDING, WITHOUT LIMITATION, ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE, OR NON-INFRINGEMENT OF THIRD-PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for developers who are designing with Renesas products. You are solely responsible for (1) selecting the appropriate products for your application, (2) designing, validating, and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, or other requirements. These resources are subject to change without notice. Renesas grants you permission to use these resources only to develop an application that uses Renesas products. Other reproduction or use of these resources is strictly prohibited. No license is granted to any other Renesas intellectual property or to any third-party intellectual property. Renesas disclaims responsibility for, and you will fully indemnify Renesas and its representatives against, any claims, damages, costs, losses, or liabilities arising from your use of these resources. Renesas' products are provided only subject to Renesas' Terms and Conditions of Sale or other applicable terms agreed to in writing. No use of any Renesas resources expands or otherwise alters any applicable warranties or warranty disclaimers for these products.

(Disclaimer Rev.1.01 Jan 2024)

#### **Corporate Headquarters**

TOYOSU FORESIA, 3-2-24 Toyosu, Koto-ku, Tokyo 135-0061, Japan www.renesas.com

#### Trademarks

Renesas and the Renesas logo are trademarks of Renesas Electronics Corporation. All trademarks and registered trademarks are the property of their respective owners.

#### **Contact Information**

For further information on a product, technology, the most up-to-date version of a document, or your nearest sales office, please visit <u>www.renesas.com/contact-us/</u>.

# **Mouser Electronics**

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

**Renesas Electronics:** 

SLG5NT1533V